# N-Channel 30-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

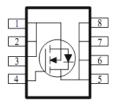
# **Typical Applications:**

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)		
30	13 @ V <sub>GS</sub> = 10V	14		
30	18 @ $V_{GS} = 4.5V$	12		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			30	V			
Gate-Source Voltage	$V_{GS}$	±20	V				
Continuous Drain Current a	T <sub>A</sub> =25°C	l <sub>D</sub>	14				
Continuous Drain Current	T <sub>A</sub> =70°C	'D	11	Α			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	50					
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	5.1	Α				
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3.5	W			
Fower Dissipation	T <sub>A</sub> =70°C	' D	2	VV			
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

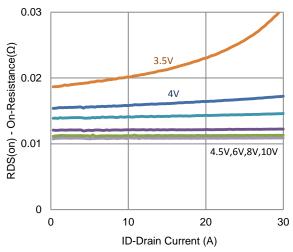
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zoro Coto Voltogo Droin Correct	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 11 \text{ A}$	13		13	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 8.8 \text{ A}$			18	11122	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 11 \text{ A}$		25		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		15			
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 11 \text{ A}$		5.7		nC	
Gate-Drain Charge	$Q_gd$	1D = 11 A		6.3			
Turn-On Delay Time	t <sub>d(on)</sub>			7			
Rise Time	t <sub>r</sub>	$V_{DS} = 15 \text{ V}, R_L = 1.4 \Omega, I_D = 11 \text{ A},$		15		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		40		ns	
Fall Time	t <sub>f</sub>			22			
Input Capacitance	C <sub>iss</sub>			1456			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		231		pF	
Reverse Transfer Capacitance	$C_{rss}$			198			

#### Notes

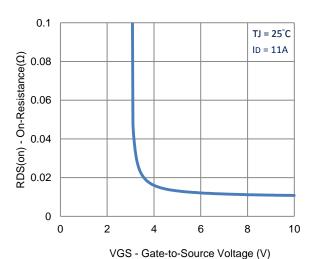
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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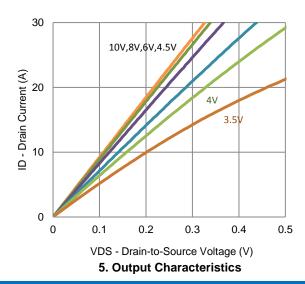
### **Typical Electrical Characteristics**

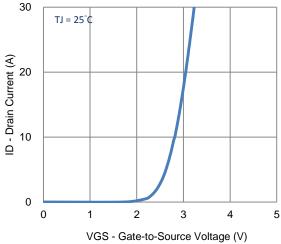


#### 1. On-Resistance vs. Drain Current

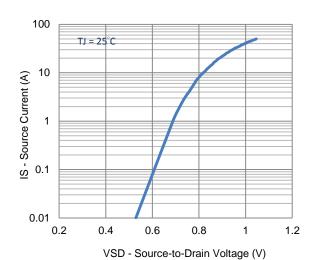


3. On-Resistance vs. Gate-to-Source Voltage

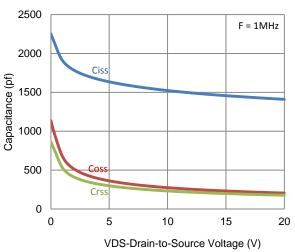




2. Transfer Characteristics



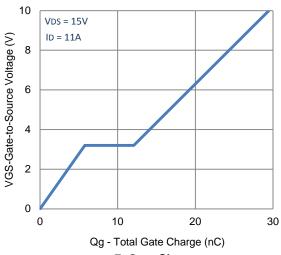
4. Drain-to-Source Forward Voltage

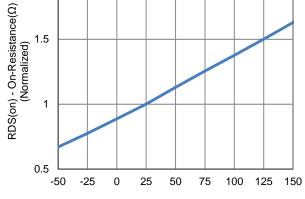


6. Capacitance

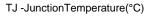
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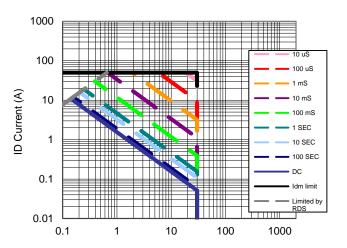
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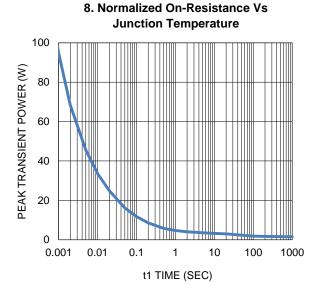




7. Gate Charge



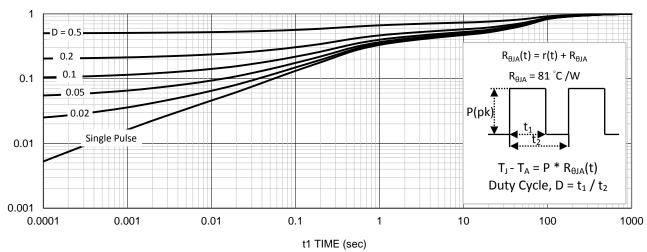




VDS Drain to Source Voltage (V)

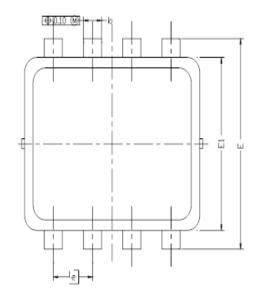
9. Safe Operating Area

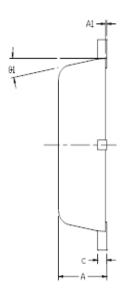
10. Single Pulse Maximum Power Dissipation

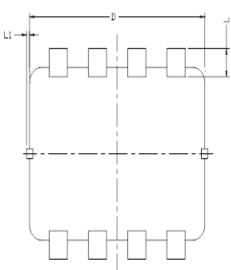


11. Normalized Thermal Transient Junction to Ambient

# Package Information







DIM.	MILLIMETERS			INCHES			
יואודת	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0,900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0,000		0,002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
_	0.08	0.152	0.25	0.003	0,006	0.010	
D	2.90 BSC			0.114 BSC			
E	2.80 BSC			0.110 BSC			
E1	2.30 BSC			0.091 BSC			
6	0.65 BSC			0.026 BSC			
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0	10	12	0	10	12	